

High-average-power Picosecond Drive Source For Photocathode Injectors

Alex Dergachev, Mikhail A. Yakshin and Peter F. Moulton

Q-Peak, Inc.

135 South Road, Bedford, Massachusetts 01730

E-mail: dergachev@qpeak.com

Carsten Janke, Marco Benetti and Thomas Ruchti

Time-Bandwidth Products AG,

Technoparkstrasse 1, 8005 Zurich, Switzerland

E-mail: tr@tbwp.com

Michelle Shinn

Thomas Jefferson National Accelerator Facility

12000 Jefferson Ave, Newport News, VA 23606

E-mail: shinn@jlab.org



Achieving High Repetition Rate

High Gain and Short Lifetime are required:

=> Nd:YVO₄ master oscillator and Nd:YVO₄ MOPA ???

Nd:YVO₄ material for the amplifiers:

- ❑ Limited size of high-quality crystals
- ❑ Large dn/dT:
 - strong, aberrated thermal lensing
 - difficulty with power scaling by adding amplifiers

⇒ *challenges in scaling up to high powers*

- ❑ Natural birefringence
 - no depolarization in amplifiers

Our Preferred approach

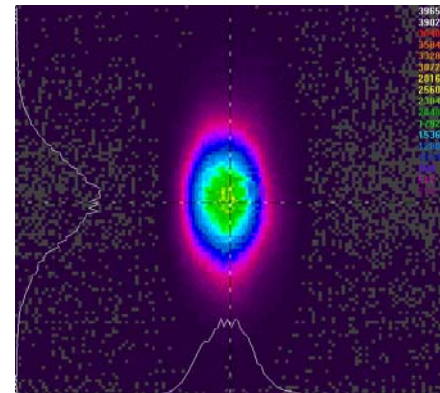
Develop a frequency-doubled Nd:YVO₄ MOPA system:

- ❑ Low-power (0.5-1 W), end-pumped, passively mode-locked laser as a master oscillator
- ❑ Nd:YVO₄ is a best suited material for high rep.rate mode-locked osc
 - Highest gain
- ❑ MO defines almost all critical parameters :
 - Repetition rate
 - Pulseswidth
 - Timing jitter
 - Wavelength
 - Beam pointing
- ❑ Power amplifier based on a number of MPV gain modules
- ❑ Amplifier chain defines:
 - Max average power
 - Beam quality
 - Beam pointing

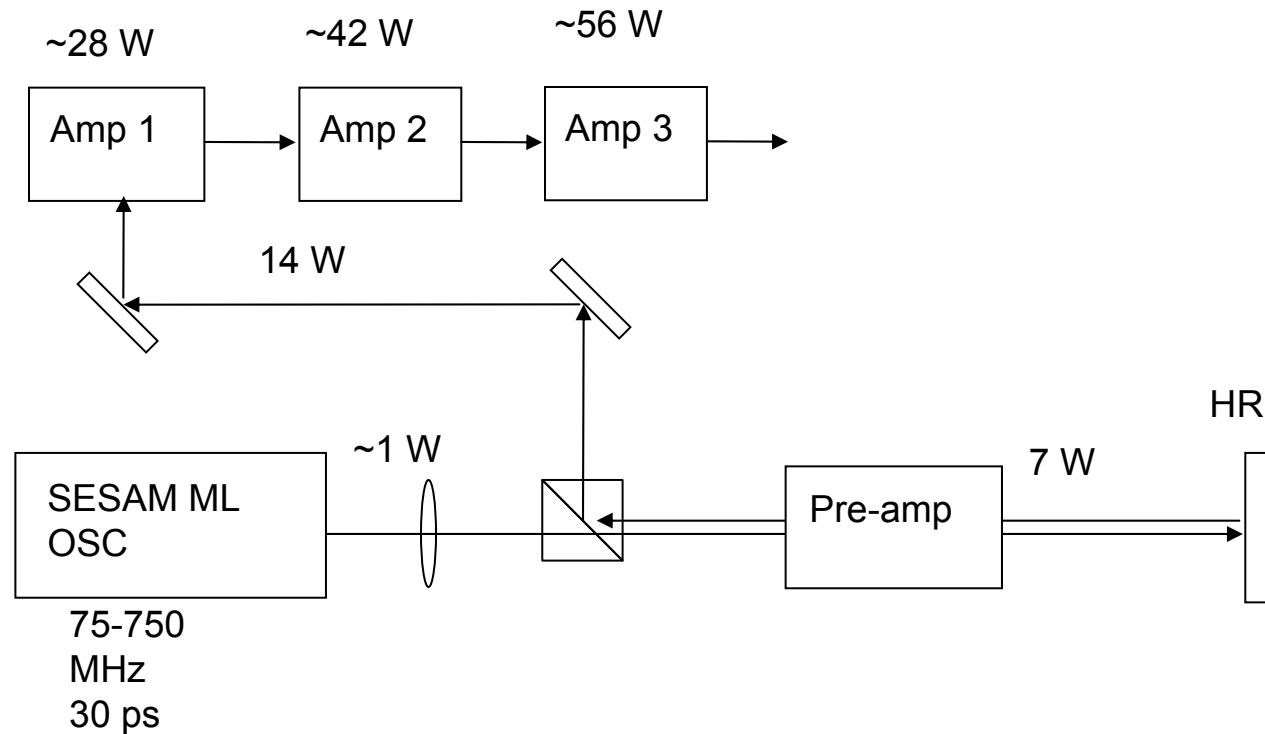
Nd:YVO₄ Master Oscillator (Time-Bandwidth AG)

Laser Model: GE-100-VAN-74.85/748.5-CLX

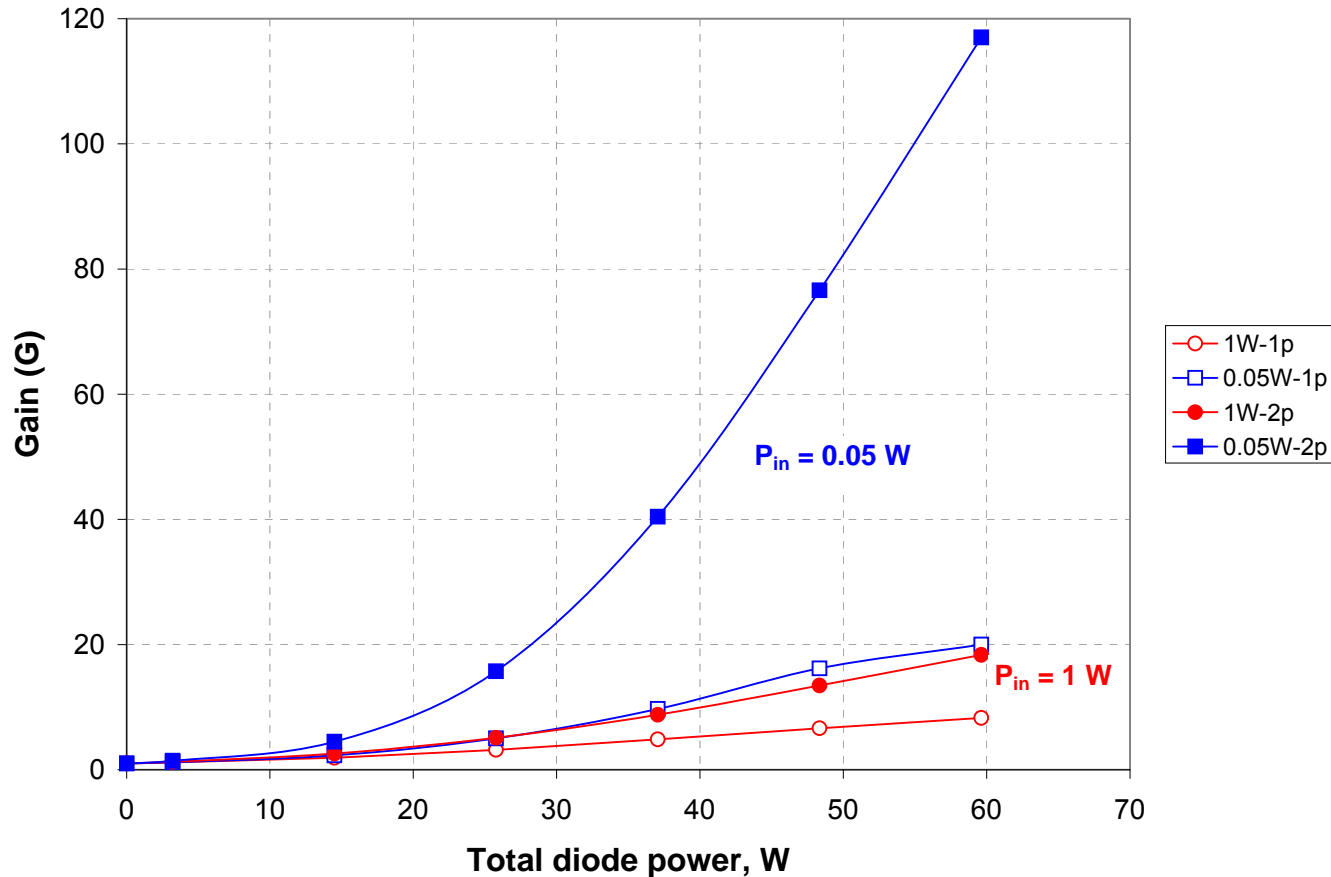
- Diode pumped solid state laser system
- Passively mode-locked by patented SESAM[®] technology of Time-Bandwidth Products AG
- Switchable repetition rates:
 - 74.85 MHz or 748.5 MHz
 - Active locking to an external RF source
 - Timing jitter < 400 fs rms.
- Wavelength: 1064 nm
- Output power: >950 mW
- Pulsewidth optionally increased to 30 ps ± 5 ps
- Diffraction limited beam
 - M² (X ≤ 1.1, Y ≤ 1.2)



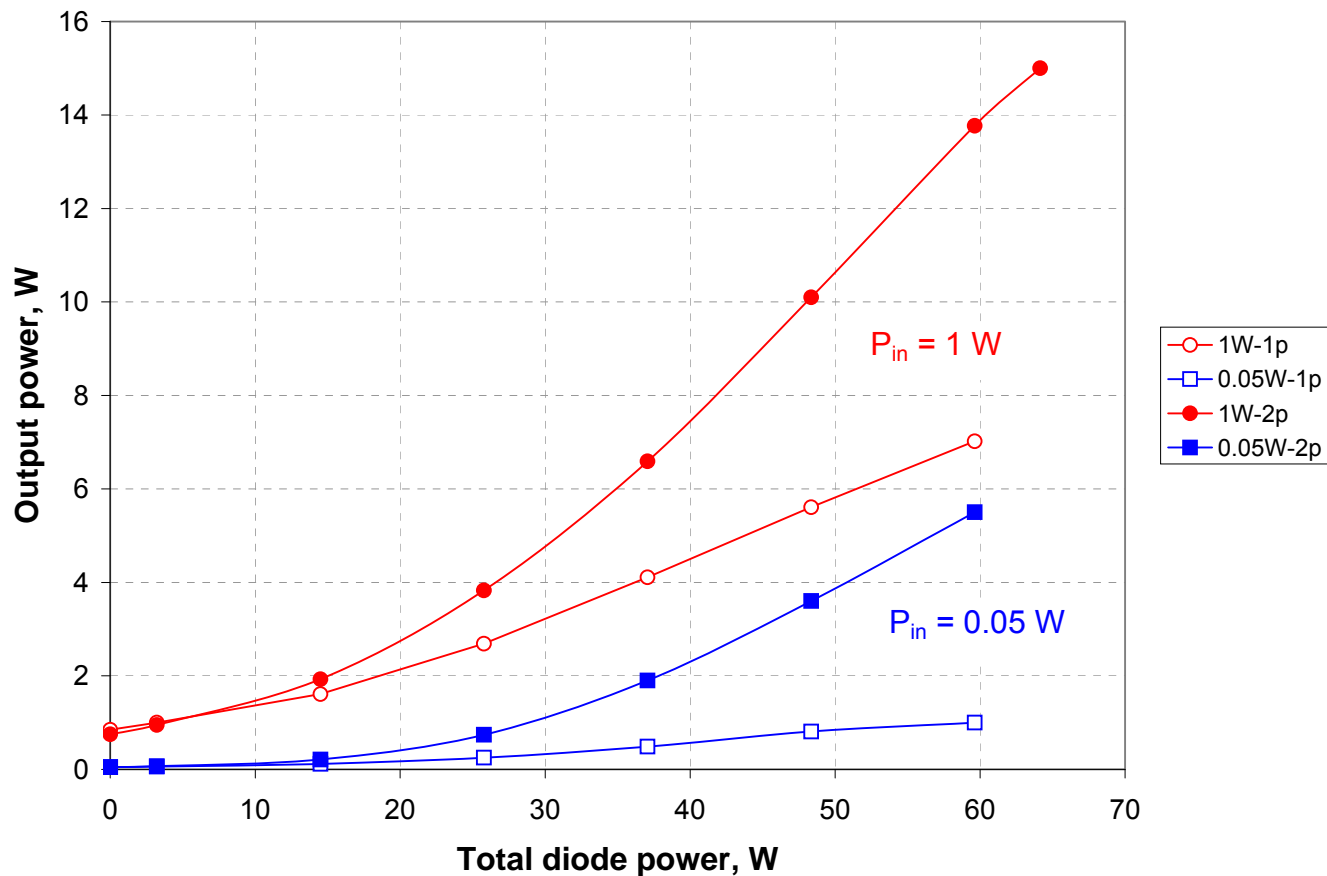
PS High-Repetition Rate Nd:YVO₄ MOPA



Pre-Amplifier Performance – 1- and 2-Pass Gain



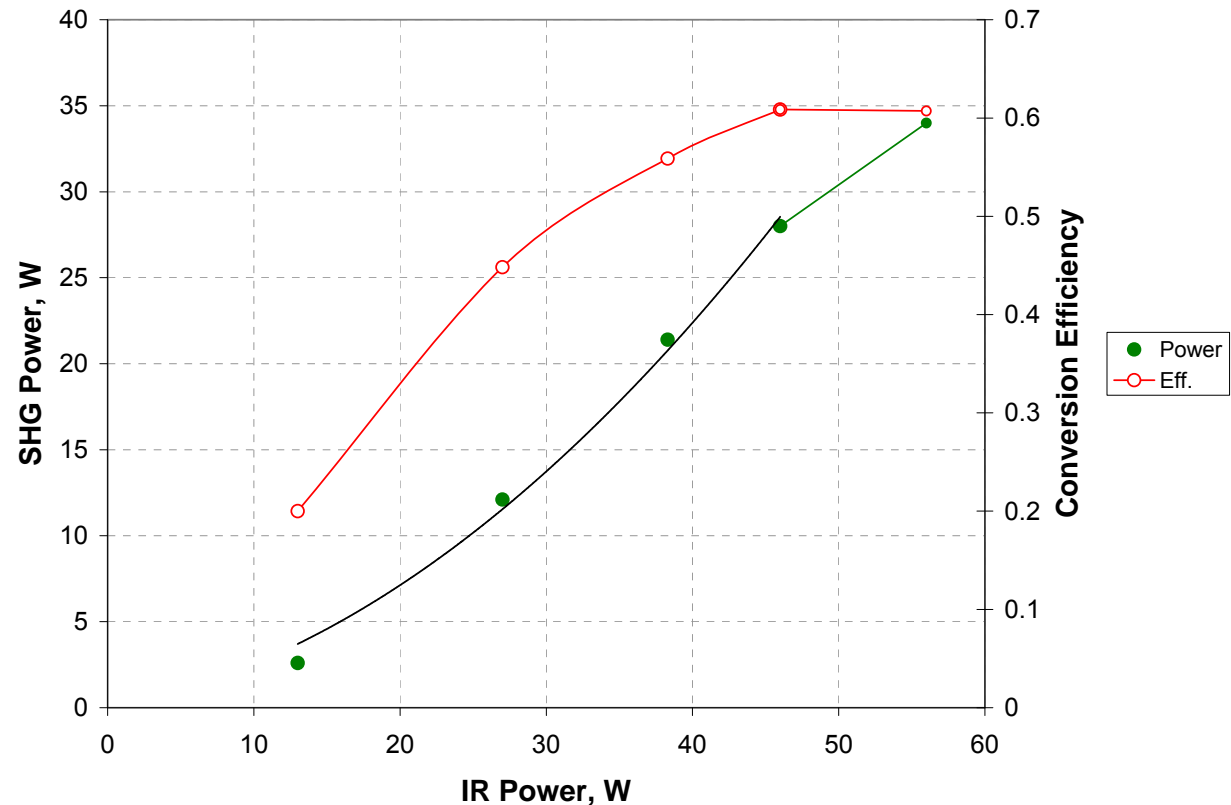
Pre-Amplifier Performance –1- and 2-Pass Power Output



SHG in LBO

- ≤ 34 W at 532 nm
- $\geq 60\%$ eff.
- 75 MHz
- TEM_{00}

- ≤ 10 W at 532 nm
- $\leq 18\%$ eff.
- 750 MHz
- TEM_{00}



Typical performance at 75 MHz